

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

248145US2S

SERIAL NO. 10/765,031
New Application

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Yoshihisa IWATA, et al.

FILING DATE

Herewith

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
NN	AA	6,081,445	06/27/00	Jing SHI, et al.			
NN	AB	6,163,473	12/19/00	Lung T. TRAN			
NN	AC	6,205,051	03/20/01	James A. BRUG, et al.			
	AD						
	AE						
	AF						
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	AJ						
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	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO
	AO				
	AP				
	AQ				
	AR				
	AS				

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

NN	AT	Roy SCHEUERLEIN, et al., "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", 2000 IEEE INTERNATIONAL SOLID-STATE CIRCUITS CONFERENCE, ISSCC 2000, DIGEST OF TECHNICAL PAPERS, TD: EMERGING MEMORY & DEVICE TECHNOLOGIES, Session 7, Paper TA 7.2, February 2000, 6 pages
I	AU	M. DURLAM, et al., "Nonvolatile RAM based on Magnetic Tunnel Junction Elements", 2000 IEEE INTERNATIONAL SOLID-STATE CIRCUITS CONFERENCE, ISSCC 2000, DIGEST OF TECHNICAL PAPERS, TD: EMERGING MEMORY & DEVICE TECHNOLOGIES, Session 7, Paper TA 7.3, February 2000, 6 pages
	AV	Takeshi HONDA, et al., "MRAM-Writing Circuitry to Compensate for Thermal-Variation of Magnetization-Reversal Current", 2002 SYMPOSIUM ON VLSI CIRCUITS DIGEST OF TECHNICAL PAPERS, 12-3, June 2002, 2 pages
	AW	M. MOTOYOSHI, et al., "High-Performance MRAM Technology with an Improved Magnetic Tunnel Junction Material", 2002 SYMPOSIUM ON VLSI DIGEST OF TECHNICAL PAPERS, 21.4, June 2002, Pages 212-213
	AX	Manoj BHATTACHARYYA, et al., "Thermal Variations in Switching Fields for Sub-Micron MRAM Cells", IEEE TRANSACTIONS ON MAGNETICS, Vol. 37, No. 4, July 2001, Pages 1970-1972
	AY	Ricardo C. SOUSA, et al., "Dynamic Switching of Tunnel Junction MRAM Cell with Nanosecond Field Pulses", IEEE TRANSACTIONS ON MAGNETICS, Vol. 36, No. 5, September 2000, Pages 2770-2772
PN	AZ	Paul R. GRAY, et al., "Analysis and Design of Analog Integrated Circuits-2 nd Edition" Japanese Edition, 1 st Y. IWATA Volume, Pages 270-276
<input type="checkbox"/> Additional References sheet(s) attached		

Examiner

N. A. M. H. W. J. M.

Date Considered

9/13/05

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



LIST OF RELATED CASES

<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Inventor/ Applicant</u>	<u>Client's Reference Number</u>
248145US2S*	10/765,131	01/28/04	IWATA et al.	ACG035274-USA-A T1NK-02S1435
251023US2S	10/807,454	03/24/04	IWATA et al.	ACG036525-USA-A T1HS-03S1460

Considered 9/13/05

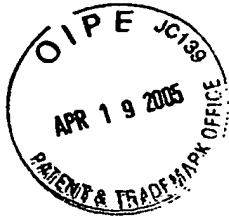
Nam Nguyen



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<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Inventor/ Applicant</u>
248145US2S*	10/765,131	01/28/04	IWATA et al.
255901US2S	10/890,455	07/14/04	IWATA

Considered 3/13/05
Namguyen



LIST OF RELATED CASES

<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Patent Appl. Publication No.</u>	<u>Inventor/ Applicant</u>
248145US2S*	10/765,131	01/28/04	2004-0252551	IWATA et al.
264846US2S	11/037,108	01/19/05		IWATA

Considered 9/13/05
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LIST OF RELATED CASES

<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Inventor/ Applicant</u>
237768US2S	10/438,015	05/15/03	IWATA et al.

Considered 9/13/05
Nam Nguyen